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(54) METHOD FOR PRODUCING A SEMICONDUCTIVE DEVICE COMPRISING A BACK GATE

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(57)ABSTRACT

A method is provided for producing a back gate under a semiconductive device surrounded by isolation trenches. The method includes a partial etching of the isolation trenches forming an opening to the sacrificial layer, a selective removal of the sacrificial layer forming a cavity under the device, and a filling of the cavity with a conductive material so as to form the back gate. Advantageously, the formation of the isolation trenches comprises a formation of a sacrificial coating layer at the flanks of the trenches, in contact with the sacrificial layer, before filling with an isolating material, and the partial etching of the trenches comprises a removal of this sacrificial coating layer selectively at the isolating material.



